



LAPD-1-09-17-CHIP



TECHNICAL DATA

Photodiode Chip die

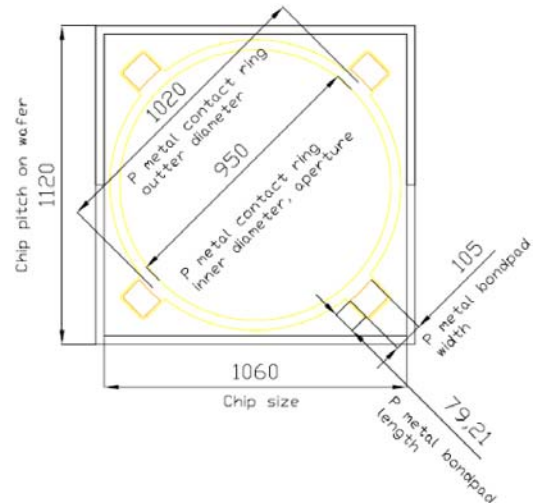
InGaAs

LAPD-1-09-17-CHIP adopt InGaAs pin structure based on InP by MOCVD method and planar diffusing technology. The active area is \varnothing 1 mm respectively.



Absolute Maximum Ratings

Item	Symbol	Value	Unit
Reverse Voltage	U_R	20	V
Reverse Current	I_R	20	mA
Forward current	I_F	10	mA
Operating Temperature	T_{opr}	-20 ... +85	°C
Storage Temperature	T_{stg}	-40 ... +85	°C



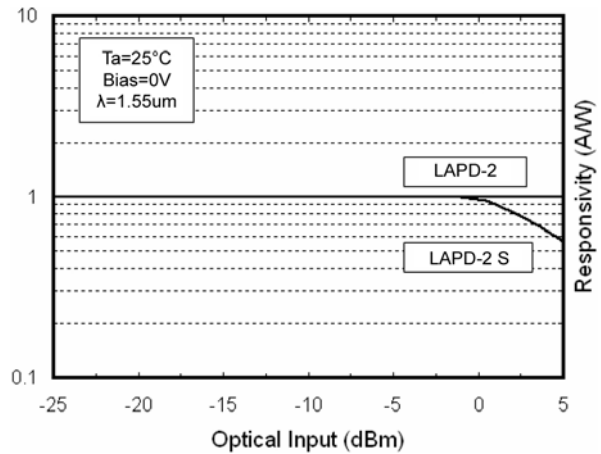
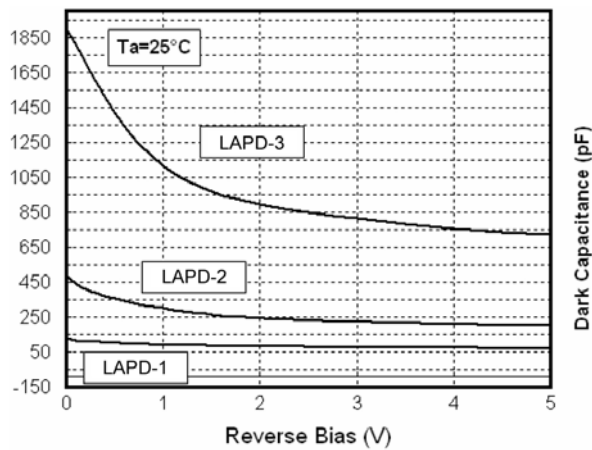
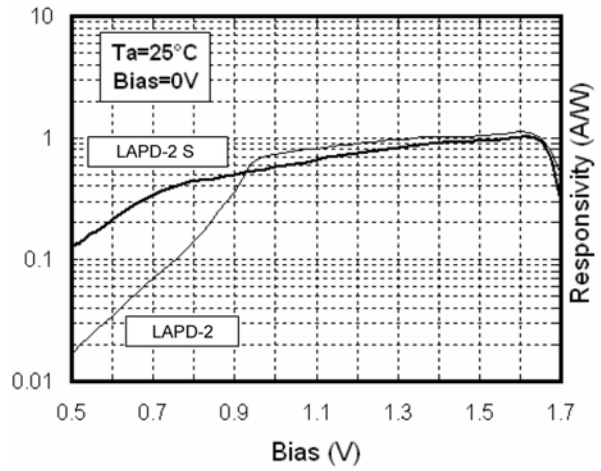
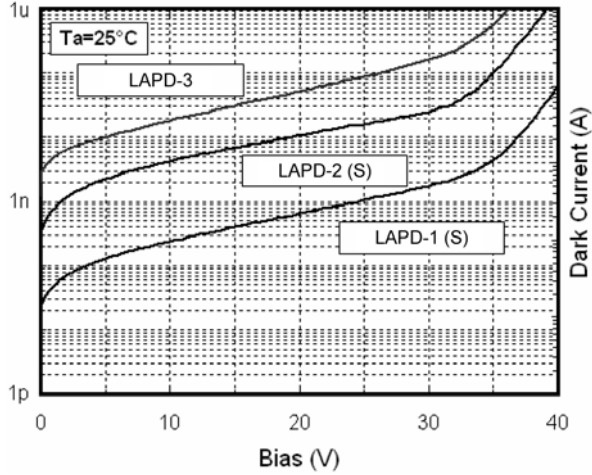
Specifications

Item	Min.	Typ.	Max.	Unit
Wavelength Range	0.9 .. 1.7			μm
Active Area	\varnothing 1			mm
Saturation Power	1550 nm	-	-3	dBm
Specific Detectivity (D^*)	1550 nm	2.5	5	10^{12} Jones
Responsibility (0 V)	650 nm	0.02	0.05	A/W
	850 nm	0.10	0.20	
	1310 nm	0.80	0.90	
	1550 nm	0.85	0.95	
Capacitance	0 V	-	140	pF
	-5 V	-	70	
Dark Current	-5 V	-	2	nA
Shunt Resistance	25	80	-	M Ω
Chip Size	1060 x 1060			μm
Chip Thickness	300			μm

Packing: Chips on adhesive film



Typical Performance Curves



LAPD-2 Spatial Response
Ta=25°C, Bias=0V, λ=1550nm

